

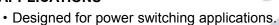


isc Silicon NPN Power Transistor

DESCRIPTION

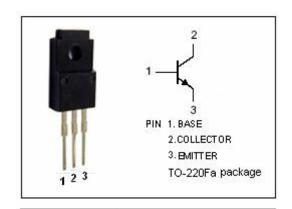
- · Collector-Emitter Breakdown Voltage-
- : V_{(BR)CEO}= 60V(Min.)
- · High Speed Switching
- · Good Linearity of hFE
- High Collector Power Dissipation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

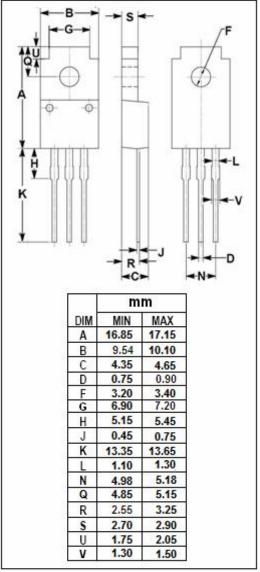
APPLICATIONS



ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{СВО}	Collector-Base Voltage	80	V	
V _{CEO}	Collector-Emitter Voltage	60	V	
V _{EBO}	Emitter-Base Voltage	6	V	
Ic	Collector Current-Continuous	4	Α	
I _B	Base Current- Continuous	1	Α	
D	Collector Power Dissipation @ T _a =25℃	2		
Pc	Collector Power Dissipation @ Tc=25℃	35	W	
TJ	Junction Temperature	150 °C		
T _{stg}	Storage Temperature Range	-55~150	$^{\circ}$	







isc Silicon NPN Power Transistor

2SD2000

ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

10 20 0 01	10-20 © unless otherwise specified								
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 25mA; I _B = 0	60			V			
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 4A; I _B = 0.4A			1.5	٧			
V _{BE(on)}	Base-Emitter On Voltage	I _C = 4A; V _{CE} = 4V			2.0	V			
I _{CBO}	Collector Cutoff Current	V _{CB} = 80V; I _E = 0			100	μ Α			
I _{EBO}	Emitter Cutoff Current	V _{EB} = 6V; I _C = 0			100	μ Α			
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 4V	70		250				
h _{FE-2}	DC Current Gain	I _C = 4A; V _{CE} = 4V	20						
f⊤	Current-Gain—Bandwidth Product	I _C = 0.2A; V _{CE} = 12V; f= 10MHz		80		MHz			
Switching Times									
ton	Turn-on Time	7		0.3		μS			
t _{stg}	Storage Time	V_{CC} = 50V, I_C = 4A; I_{B1} = I_{B2} = 0.4A		1.0		μS			
t _f	Fall Time			0.2		μS			

♦ h_{FE-1} Classifications

Q	Р		
70-150	120-250		

NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

isc website: www.iscsemi.com

isc & iscsemi is registered trademark